

(19) World Intellectual Property Organization  
International Bureau



(43) International Publication Date  
22 June 2006 (22.06.2006)

PCT

(10) International Publication Number  
**WO 2006/064822 A1**

(51) International Patent Classification:  
H03K 19/0175 (2006.01)

(21) International Application Number:  
PCT/JP2005/022901

(22) International Filing Date:  
7 December 2005 (07.12.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
2004-360636 13 December 2004 (13.12.2004) JP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AF, AG, AI, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

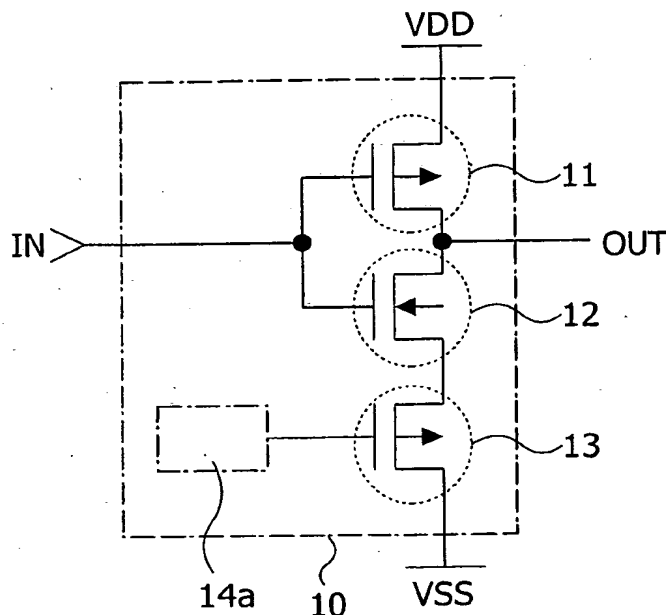
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SI, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR DEVICE AND ELECTRONIC APPLIANCE USING THE SAME



(57) Abstract: A semiconductor device with less power consumption and an electronic appliance using the same. The semiconductor device of the invention is supplied with a first potential from a high potential power source and a second potential from a low potential power source. Upon input of a first signal to an input node, an output node outputs a second signal. With the semiconductor device of the invention, a potential difference of the second signal can be controlled to be smaller than a potential difference between the first potential and the second potential, thereby power consumption required for charging/discharging wires can be reduced.